

Si PIN photodiode

S7379-01, S6695-01, S6058, S7547

Quadrant photodiode / plastic package



These Si PIN photodiodes have a quadrant element molded into clear plastic packages, and feature high sensitivity, low noise and low cross-talk. S7547 is specifically developed for violet laser detection, providing greatly improved sensitivity at $\lambda=410$ nm.

Custom-designed devices (with different element shapes, number of elements, characteristics and packages) are also available to meet your specific needs. Feel free to contact our sales office.

Features

- Clear plastic package (4 × 4.8 mm)
- High sensitivity
- Uniform element characteristic
- Low cross-talk
- Low noise

Applications

- Signal readout for CD, DVD and MO (Magneto Optical) disc
- Laser beam alignment
- Position detection, etc.
- Violet laser detection (S7547)
- Optical disc (DVD, etc.) pickup using violet laser (S7547)

■ General ratings / Absolute maximum ratings

Type No.	Dimensional outline	Active area (mm)	Elements gap (μ m)	Absolute maximum ratings		
				Reverse voltage V_R Max. (V)	Operating temperature T_{opr} ($^{\circ}$ C)	Storage temperature T_{stg} ($^{\circ}$ C)
S7379-01	①	ϕ 1.0/4 element	20	20	-25 to +85	-40 to +100
S6695-01	②	2.0 × 2.0/4 element	15			
S6058	③	0.6 × 1.2/4 element	10			
S7547						

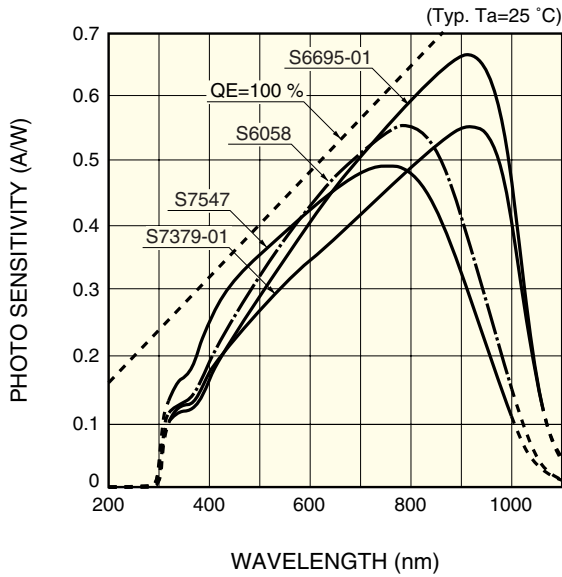
■ Electrical and optical characteristics (Typ. $T_a=25$ $^{\circ}$ C, unless otherwise noted, per 1 element)

Type No.	Spectral response range λ (nm)	Peak sensitivity wavelength λ_p (nm)	Photo sensitivity S		Dark current I_D $V_R=10$ V All elements		Temp. coefficient of I_D T_{CID} (times/ $^{\circ}$ C)	Cut-off frequency f_c $V_R=10$ V $R_L=50$ Ω $\lambda=830$ nm (MHz)	Terminal capacitance C_t $V_R=10$ V $f=1$ MHz (pF)	NEP $V_R=10$ V (W/Hz $^{1/2}$)
			$\lambda=\lambda_p$ (A/W)	$\lambda=410$ nm (A/W)	Typ. (nA)	Max. (nA)				
S7379-01	320 to 1060	900	0.55	0.19	0.04	0.2	1.15	80	1	6.5×10^{-15}
S6695-01			0.65	0.18	0.1 *1	1 *1		40 *1	3 *1	8.7×10^{-15} *1
S6058	320 to 1000	800	0.55	0.21	0.04 *2	0.2 *2		150 *2	1 *2	6.5×10^{-15} *2
S7547			760	0.5	0.27	0.01 *2		0.2 *2	500 *2	2 *2

*1: $V_R=5$ V

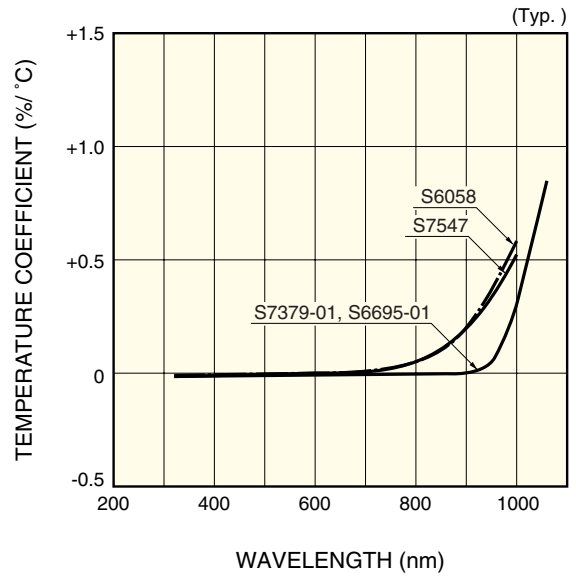
*2: $V_R=3$ V

■ Spectral response



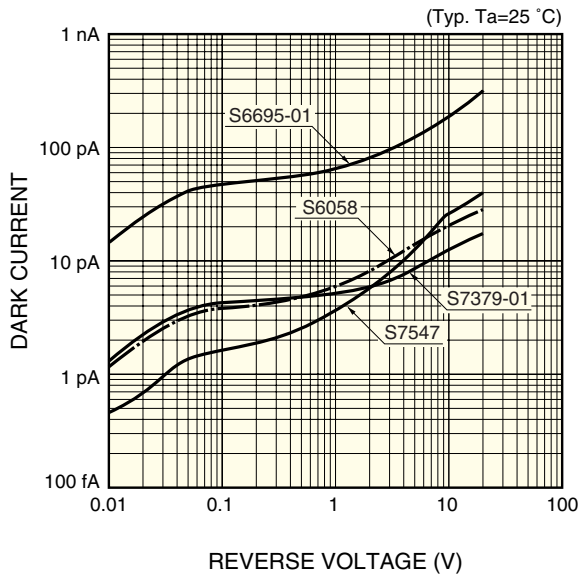
KMPDB0145EA

■ Photo sensitivity temperature characteristics



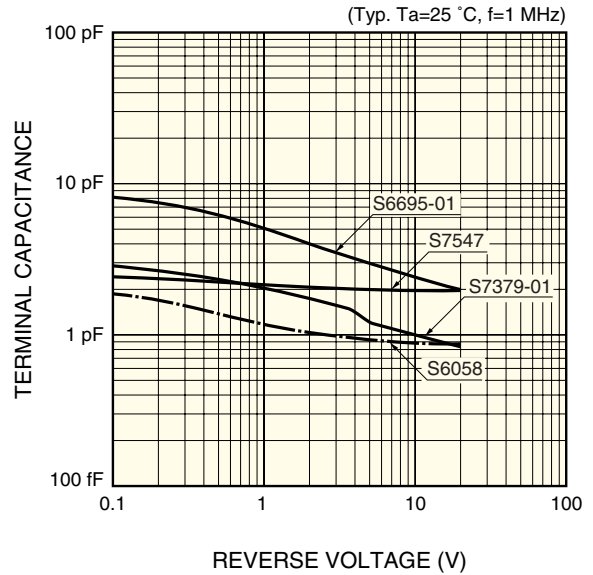
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■ Dark current vs. reverse voltage



KMPDB0147EA

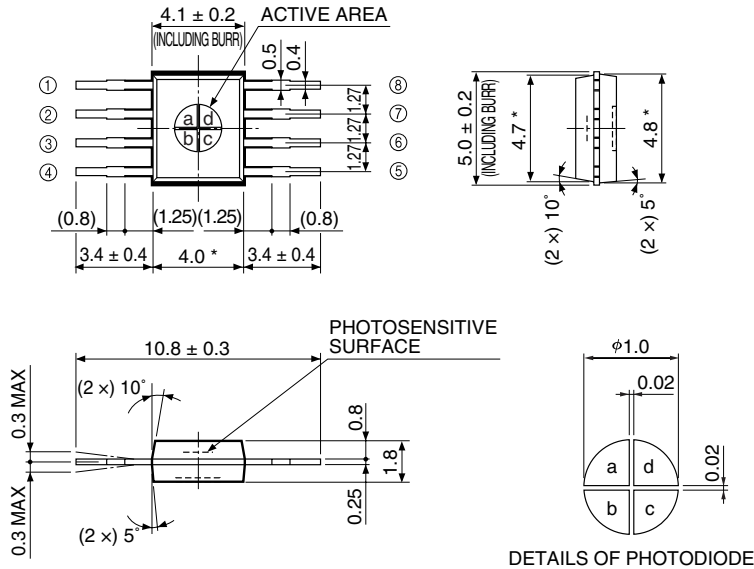
■ Terminal capacitance vs. reverse voltage



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■ Dimensional outlines (unit: mm, tolerance unless otherwise noted: ±0.1)

① S7379-01

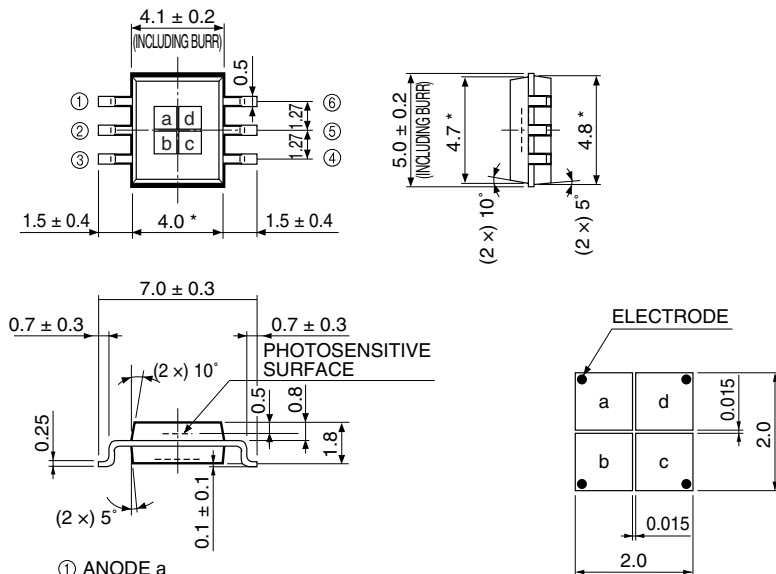


- ① NC
- ② ANODE a
- ③ ANODE b
- ④ CATHODE COMMON
- ⑤ NC
- ⑥ ANODE c
- ⑦ ANODE d
- ⑧ CATHODE COMMON

Chip position accuracy with respect to the package dimensions marked *
 $X, Y \leq \pm 0.2$
 $\theta \leq \pm 2^\circ$

KMPDA0137EA

② S6695-01

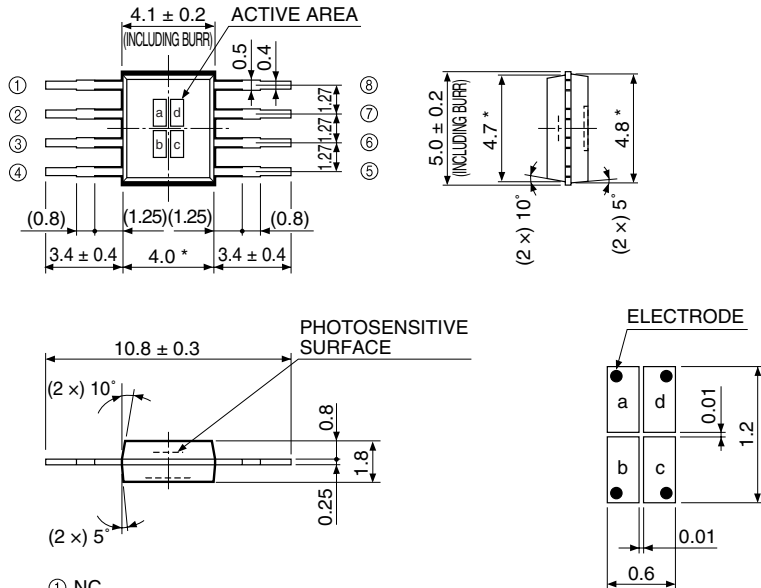


- ① ANODE a
- ② CATHODE COMMON
- ③ ANODE b
- ④ ANODE c
- ⑤ CATHODE COMMON
- ⑥ ANODE d

Chip position accuracy with respect to the package dimensions marked *
 $X, Y \leq \pm 0.2$
 $\theta \leq \pm 2^\circ$

KMPDA0121EA

③ S6058, S7547



- ① NC
- ② ANODE a
- ③ ANODE b
- ④ CATHODE COMMON
- ⑤ NC
- ⑥ ANODE c
- ⑦ ANODE d
- ⑧ CATHODE COMMON

DETAILS OF PHOTODIODE

Chip position accuracy with respect to the package dimensions marked *
 $X, Y \leq \pm 0.2$
 $\theta \leq \pm 2^\circ$

KMPDA0007EB